HEF4528B

Dual monostable multivibrator Rev. 7 — 22 November 2011

Product data sheet

General description 1.

The HEF4528B is a dual retriggerable-resetable monostable multivibrator. Each multivibrator has an active LOW input (nA), and active HIGH input (nB), an active LOW clear direct input (nCD), an output (nQ) and its complement (nQ), and two external timing component connecting pins (nCEXT, always connected to ground, and nREXT/CEXT).

An external timing capacitor (C_{EXT}) must be connected between nCEXT and nREXT/CEXT and an external resistor (REXT) must be connected between nREXT/CEXT and V_{DD}. The output pulse duration is determined by the external timing components C_{EXT} and R_{EXT}. A HIGH-to-LOW transition on nA when nB is LOW or a LOW-to-HIGH transition on nB when nA is HIGH produces a positive pulse (LOW-HIGH-LOW) on nQ and a negative pulse (HIGH-LOW-HIGH) on nQ if the nCD is HIGH. A LOW on nCD forces nQ LOW, nQ HIGH and inhibits any further pulses until nCD is HIGH.

It operates over a recommended V_{DD} power supply range of 3 V to 15 V referenced to V_{SS} (usually ground). Unused inputs must be connected to V_{DD}, V_{SS}, or another input.

Features and benefits 2.

- Fully static operation
- 5 V, 10 V, and 15 V parametric ratings
- Standardized symmetrical output characteristics
- Specified from -40 °C to +85 °C
- Complies with JEDEC standard JESD 13-B

3. **Ordering information**

Ordering information

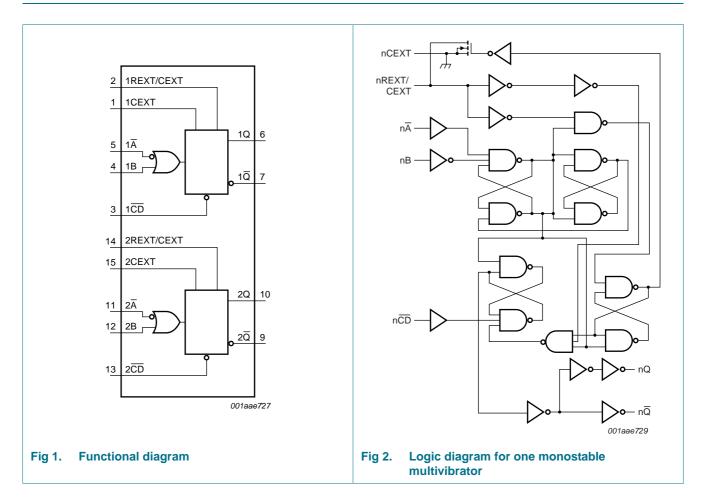
All types operate from -40 °C to +85 °C.

Type number	Package		
	Name	Description	Version
HEF4528BP	DIP16	plastic dual in-line package; 16 leads (300 mil)	SOT38-4
HEF4528BT	SO16	plastic small outline package; 16 leads; body width 3.9 mm	SOT109-1



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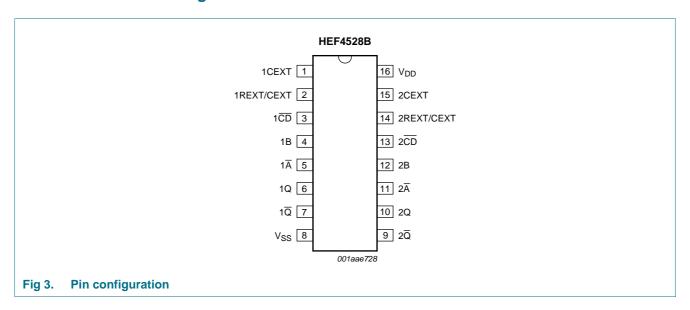
4. Functional diagram



Dual monostable multivibrator

5. Pinning information

5.1 Pinning



5.2 Pin description

Table 2. Pin description

Symbol	Pin	Description
1CEXT, 2CEXT	1, 15	external capacitor connection (always connected to ground)
1REXT/CEXT, 2REXT/CEXT	2, 14	external capacitor/resistor connection
1CD, 2CD	3, 13	clear direct input (active LOW)
1B, 2B	4, 12	input (LOW-to-HIGH triggered)
1 A , 2 A	5, 11	input (HIGH-to-LOW triggered)
1Q, 2Q	6, 10	output
1Q, 2Q	7, 9	complementary output (active LOW)
V _{SS}	8	ground supply voltage
V_{DD}	16	supply voltage

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6. Functional description

Table 3. Function table[1]

Inputs			Outputs			
Ā	В	CD	Q	Q		
\	L	Н	Л	Т		
Н	\uparrow	Н	Л	T		
Χ	X	L	L	Н		

^[1] H = HIGH voltage level; L = LOW voltage level; X = don't care;

 \square = one HIGH level output pulse, with the pule width determined by C_{EXT} and R_{EXT};

7. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to $V_{SS} = 0 \text{ V}$ (ground).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{DD}	supply voltage		-0.5	+18	V
I _{IK}	input clamping current	$V_I < -0.5 \text{ V or } V_I > V_{DD} + 0.5 \text{ V}$	-	±10	mA
VI	input voltage		-0.5	$V_{DD} + 0.5$	V
l _{OK}	output clamping current	$V_I < -0.5 \text{ V or } V_I > V_{DD} + 0.5 \text{ V}$	-	±10	mA
I _{I/O}	input/output current		-	±10	mA
I _{DD}	supply current		-	50	mA
T _{stg}	storage temperature		-65	+150	°C
T _{amb}	ambient temperature		-40	+85	°C
P _{tot}	total power dissipation	$T_{amb} = -40 ^{\circ}\text{C} \text{ to } +85 ^{\circ}\text{C}$			
		DIP16 package	<u>[1]</u> -	750	mW
		SO16 package	[2] -	500	mW
Р	power dissipation	per output	-	100	mW

^[1] For DIP16 package: P_{tot} derates linearly with 12 mW/K above 70 °C.

 $[\]uparrow$ = positive-going transition; \downarrow = negative-going transition;

 $[\]square$ = one LOW level output pulse, with the pulse width determined by C_{EXT} and R_{EXT} .

^[2] For SO16 package: P_{tot} derates linearly with 8 mW/K above 70 °C.

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8. Recommended operating conditions

Table 5. Recommended operating conditions

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V_{DD}	supply voltage		3	-	15	V
VI	input voltage		0	-	V_{DD}	V
T _{amb}	ambient temperature	in free air	-40	-	+85	°C
Δt/ΔV	input transition rise and fall rate	$V_{DD} = 5 V$	-	-	3.75	μs/V
		$V_{DD} = 10 \text{ V}$	-	-	0.5	μs/V
		V _{DD} = 15 V	-	-	0.08	μs/V

9. Static characteristics

Table 6. Static characteristics

 $V_{SS} = 0$ V; $V_I = V_{SS}$ or V_{DD} ; unless otherwise specified.

Symbol	Parameter	Conditions	V _{DD}	T _{amb} =	-40 °C	T _{amb} = +25 °C		T _{amb} = +85 °C		Unit
				Min	Max	Min	Max	Min	Max	
V_{IH}	HIGH-level	$ I_{O} < 1 \mu A$	5 V	3.5	-	3.5	-	3.5	-	V
	input voltage		10 V	7.0	-	7.0	-	7.0	-	V
			15 V	11.0	-	11.0	-	11.0	-	V
V_{IL}	LOW-level	$ I_{O} < 1 \mu A$	5 V	-	1.5	-	1.5	-	1.5	V
	input voltage		10 V	-	3.0	-	3.0	-	3.0	V
			15 V	-	4.0	-	4.0	-	4.0	V
V _{OH}	HIGH-level output voltage	$ I_O < 1 \mu A$	5 V	4.95	-	4.95	-	4.95	-	V
			10 V	9.95	-	9.95	-	9.95	-	V
			15 V	14.95	-	14.95	-	14.95	-	V
V _{OL}	LOW-level output voltage	$ I_O < 1 \mu A$	5 V	-	0.05	-	0.05	-	0.05	V
			10 V	-	0.05	-	0.05	-	0.05	V
			15 V	-	0.05	-	0.05	-	0.05	V
I _{OH}	HIGH-level output current	$V_0 = 2.5 \text{ V}$	5 V	-	-1.7	-	-1.4	-	-1.1	mΑ
		$V_0 = 4.6 \text{ V}$	5 V	-	-0.52	-	-0.44	-	-0.36	mΑ
		$V_0 = 9.5 \ V$	10 V	-	-1.3	-	-1.1	-	-0.9	mΑ
		$V_0 = 13.5 \text{ V}$	15 V	-	-3.6	-	-3.0	-	-2.4	mΑ
I _{OL}	LOW-level output current	$V_0 = 0.4 \ V$	5 V	0.52	-	0.44	-	0.36	-	mΑ
		$V_0 = 0.5 \ V$	10 V	1.3	-	1.1	-	0.9	-	mΑ
		$V_0 = 1.5 \text{ V}$	15 V	3.6	-	3.0	-	2.4	-	mΑ
I _I	input leakage current		15 V	-	±0.3	-	±0.3	-	±1.0	μΑ
I _{DD}	supply current	all valid input	5 V	-	20	-	20	-	150	μΑ
		combinations; $I_O = 0 A$	10 V	-	40	-	40	-	300	μΑ
		10 = 0 A	15 V	-	80	-	80	-	600	μΑ
C _I	input capacitance		-	-	-	-	7.5	-	-	pF

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10. Dynamic characteristics

Table 7. Dynamic characteristics

 $V_{SS} = 0 \text{ V}$; $T_{amb} = 25 \text{ °C}$; for waveforms see <u>Figure 6</u>; for test circuit see <u>Figure 7</u>; unless otherwise specified.

EPHLE PATE HIGH to LOW propagation delay as e Figure 5 5 V 113 ns + (0.55 ns/pF)C _L council c	Symbol	Parameter	Conditions	V_{DD}	Extrapolation formula[1]	Min	Тур	Max	Unit
The content of the	t _{PHL}		•	5 V	113 ns + (0.55 ns/pF)C _L	-	140	280	ns
To D to nQ; see Figure 5 10 \ 29 ns + (0.23 ns/pF)C,		propagation delay	see <u>Figure 5</u>	10 V	39 ns + (0.23 ns/pF)C _L	-	50	100	ns
LOW to HIGH propagation delay NA or nB to nQ; see Figure 5 10 V 29 ns + (0.23 ns/pF)CL - 30 60 ns				15 V	27 ns + (0.16 ns/pF)C _L	-	35	70	ns
To V 29 ins Y (0.16 ns/pF)C _L 30 60 ns				5 V	78 ns + (0.55 ns/pF)C _L	•	105	210	ns
tpLH LOW to HIGH propagation delay nĀ or nB to nQ; see Figure 5 5 V 128 ns + (0.55 ns/pF)CL - 155 305 ns 15 V 49 ns + (0.23 ns/pF)CL - 60 115 ns 16 V 32 ns + (0.16 ns/pF)CL - 40 80 ns 16 V 39 ns + (0.23 ns/pF)CL - 120 240 ns 16 V 39 ns + (0.23 ns/pF)CL - 120 240 ns 16 V 27 ns + (0.16 ns/pF)CL - 100 105 ns 15 V 27 ns + (0.16 ns/pF)CL - 35 70 ns 15 V 27 ns + (0.16 ns/pF)CL - 30 60 ns 15 V 27 ns + (0.16 ns/pF)CL - 30 60 ns 15 V 9 ns + (0.23 ns/pF)CL - 30 60 ns 16 V 9 ns + (0.28 ns/pF)CL - 20 40 ns 16 V 6 ns + (0.28 ns/pF)CL - 20 40 ns			see <u>Figure 5</u>	10 V	29 ns + (0.23 ns/pF)C _L	•	40	85	ns
$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$				15 V	22 ns + (0.16 ns/pF)C _L	-	30	60	ns
15 V 32 ns + (0.16 ns/pF)C _L - 40 80 ns nCD to nQ; 5 V 93 ns + (0.15 ns/pF)C _L - 120 240 ns see Figure 5 10 V 39 ns + (0.23 ns/pF)C _L - 50 105 ns 15 V 27 ns + (0.16 ns/pF)C _L - 35 70 ns 15 V 27 ns + (0.16 ns/pF)C _L - 30 60 ns 15 V 9 ns + (0.42 ns/pF)C _L - 30 60 ns 15 V 9 ns + (0.42 ns/pF)C _L - 30 60 ns 15 V 9 ns + (0.42 ns/pF)C _L - 30 60 ns 15 V 6 ns + (0.28 ns/pF)C _L - 20 40 ns 15 V 0 -75 - ns 15 V 0 -75 - ns 15 V 0 -25 - ns 15 V 0 0 -40 - ns 15 V 0 0 -25 - ns 15 V 0 0 -25 - ns 15 V 0 0 -40 - ns 15 V 0 0 -25 - ns 15 V 0 0 0 0 0 15 V 0 0 0 0 0 15 V 0 0 0 0 0	t _{PLH}		•	5 V	128 ns + (0.55 ns/pF)C _L	-	155	305	ns
$ \begin{array}{c c c c c c c c c c c c c c c c c c c $		propagation delay	see <u>Figure 5</u>	10 V	49 ns + (0.23 ns/pF)C _L	-	60	115	ns
				15 V	32 ns + (0.16 ns/pF)C _L	-	40	80	ns
$t_{t} \text{transition time} t_{t} \text{transition time} t_{t} \text{transition time} \frac{nQ, nQ;}{see \ Figure \ 5} \frac{5 \ V}{10 \ N} \frac{27 \ ns + (0.16 \ ns/pF)C_{L}}{10 \ V} \frac{30}{9 \ ns + (0.42 \ ns/pF)C_{L}} \frac{60}{30} \frac{120}{0} ns} \frac{15 \ V}{10 \ N} \frac{9 \ ns + (0.42 \ ns/pF)C_{L}}{15 \ V} \frac{30}{0} \frac{60}{0} ns} \frac{15}{0} \frac$			· ·	5 V	93 ns + (0.55 ns/pF)C _L	-	120	240	ns
$\begin{array}{c} t_t \\ t_{rec} \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\$			see <u>Figure 5</u>	10 V	39 ns + (0.23 ns/pF)C _L	-	50	105	ns
$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$				15 V	27 ns + (0.16 ns/pF)C _L	-	35	70	ns
$t_{rec} \text{recovery time} \frac{n\overline{CD} \text{ to } n\overline{A} \text{ or } nB;}{see \ Figure \ 6} \frac{5 \ V}{10 \ V} 0 0 -75 - ns}{15 \ V} 0 0 -705 - ns}{15 \ V} 0 0 0 -705 - ns}{15 \ V} 0 0 0 - 0 0 - $	t _t	transition time		5 V	2 10 ns + (1.00 ns/pF)C _L	-	60	120	ns
$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$			see <u>Figure 5</u>	10 V	9 ns + (0.42 ns/pF)C _L	-	30	60	ns
				15 V	6 ns + (0.28 ns/pF)C _L	-	20	40	ns
$t_{SU} \text{set-up time} \begin{array}{c ccccccccccccccccccccccccccccccccccc$	t_{rec}	recovery time		5 V		0	−75	-	ns
			see <u>Figure 6</u>	10 V		0	-30	-	ns
				15 V		0	-25	-	ns
$t_{W} \text{pulse width} \begin{array}{c ccccccccccccccccccccccccccccccccccc$	t_{su}	set-up time	•	5 V		0	-105	-	ns
$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$			see Figure 6	10 V		0	-40	-	ns
$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$				15 V		0	-25	-	ns
	t_W	pulse width	•	5 V		50	25	-	ns
$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$				10 V		30	15	-	ns
$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$			300 <u>rigure o</u>	15 V		20	10	-	ns
$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$				5 V		50	25	-	ns
$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$				10 V		30	15	-	ns
$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$			See <u>rigare o</u>	15 V	:	20	10	-	ns
				5 V		60	30	-	ns
15 V 25 10 - ns nQ or nQ; 5 V 3 - 235 - ns REXT = 5 kΩ; 10 V - 155 - ns CEXT = 15 pF; see Figure 6 15 V 4 - 140 - ns nQ or nQ; 5 V 4 - 5.45 - μs REXT = 10 kΩ; CEXT = 1 nF; 10 V - 4.95 - μs				10 V		35	15	-	ns
$\begin{array}{cccccccccccccccccccccccccccccccccccc$			See <u>rigare o</u>	15 V	:	25	10	-	ns
$C_{\text{EXT}} = 15 \text{ pF};$ $\text{see } \frac{\text{Figure 6}}{\text{15 V}}$ 15 V - 140 - ns 15 N 15				5 V	[3]	•	235	-	ns
see Figure 6 15 V - 140 - ns nQ or $n\overline{Q}$; 5 V 4 - 5.45 - μs REXT = 10 kΩ; CEXT = 1 nF; 4.95 - μs				10 V		•	155	-	ns
$R_{EXT} = 10 \text{ k}\Omega;$ $C_{EXT} = 1 \text{ nF};$				15 V		•	140	-	ns
$C_{EXT} = 1 \text{ nF};$ $\frac{10 \text{ V}}{4.5 \text{ V}}$				5 V	<u>[4]</u>	-	5.45	-	μS
				10 V		-	4.95	-	μS
			C _{EXT} = 1 nF; see Figure 6	15 V		•	4.85	-	μS

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 Table 7.
 Dynamic characteristics ...continued

 $V_{SS} = 0 \text{ V}$; $T_{amb} = 25 \text{ °C}$; for waveforms see <u>Figure 6</u>; for test circuit see <u>Figure 7</u>; unless otherwise specified.

Symbol	Parameter	Conditions	V_{DD}	Extrapolation formula[1]	Min	Тур	Max	Unit
Δt_{W}	pulse width	nQ output variation over temperature range	5 V	[5]	-	±3	-	%
	variation		10 V		-	±2	-	%
			15 V		-	±2	-	%
		nQ output variation over voltage range $V_{DD}\pm 5~\%$	5 V		-	±2	-	%
			10 V		-	±1	-	%
			15 V		-	±1	-	%
R _{EXT}	external timing	see Figure 4	5 V		5	-	2	$M\Omega$
	resistor		10 V		5	-	2	$M\Omega$
			15 V		5	-	2	$M\Omega$
C_{EXT}	external timing	see Figure 4	5 V		no limit	S		
	capacitor		10 V		no limit	S		
			15 V		no limit	s		

- [1] The typical values of the propagation delay and transition times are calculated from the extrapolation formulas shown (C_L in pF).
- [2] t_t is the same as t_{THL} and t_{TLH} .
- [3] For other R_{EXT}, C_{EXT} combinations and C_{EXT} < 0.01 μ F see Figure 4.
- [4] For other R_{EXT}, C_{EXT} combinations and C_{EXT} > 0.01 μ F use formula t_W = K \times R_{EXT} \times C_{EXT}.

where: $t_W = output pulse width (s);$

 R_{EXT} = external timing resistor (Ω);

C_{EXT} = external timing capacitor (F);

 $K = 0.42 \text{ for } V_{DD} = 5 \text{ V};$

 $K = 0.32 \text{ for } V_{DD} = 10 \text{ V};$

K = 0.30 for $V_{DD} = 15 V$.

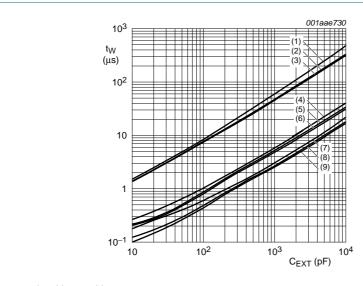
[5] $T_{amb} = -40 \,^{\circ}\text{C}$ to +85 $^{\circ}\text{C}$; Δt_W is referenced to t_W at $T_{amb} = 25 \,^{\circ}\text{C}$.

Table 8. Dynamic power dissipation P_D

 P_D can be calculated from the formulas shown. $V_{SS} = 0 \text{ V}$; $t_r = t_f \le 20 \text{ ns}$; $T_{amb} = 25 \text{ }^{\circ}\text{C}$.

Symbol	Parameter	V_{DD}	Typical formula for P_D (μ W)	where:
P_{D}	dynamic power	5 V	$P_D = 4000 \times f_i + \Sigma (f_o \times C_L) \times V_{DD}{}^2$	f _i = input frequency in MHz;
dissipation	dissipation	10 V	$P_D = 20000 \times f_i + \Sigma(f_o \times C_L) \times V_{DD}^2$	f _o = output frequency in MHz;
		15 V	$P_D = 59000 \times f_i + \Sigma (f_0 \times C_L) \times V_{DD}^2$	C_L = output load capacitance in pF;
				V_{DD} = supply voltage in V;
				$\Sigma(f_0 \times C_L)$ = sum of the outputs.

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- (1) $R_{EXT} = 100 \text{ k}\Omega$, $V_{DD} = 5 \text{ V}$.
- (2) $R_{EXT} = 100 \text{ k}\Omega$, $V_{DD} = 10 \text{ V}$.
- (3) $R_{EXT} = 100 \text{ k}\Omega$, $V_{DD} = 15 \text{ V}$.
- (4) $R_{EXT} = 10 \text{ k}\Omega$, $V_{DD} = 5 \text{ V}$.
- (5) $R_{EXT} = 10 \text{ k}\Omega$, $V_{DD} = 10 \text{ V}$.
- (6) $R_{EXT} = 10 \text{ k}\Omega$, $V_{DD} = 15 \text{ V}$.
- (7) $R_{EXT} = 5 \text{ k}\Omega$, $V_{DD} = 5 \text{ V}$.
- (8) $R_{EXT} = 5 \text{ k}\Omega$, $V_{DD} = 10 \text{ V}$.
- (9) $R_{EXT} = 5 \text{ k}\Omega$, $V_{DD} = 15 \text{ V}$.

Fig 4. Output pulse width (t_W) as a function of external timing capacitor (C_{EXT})

Dual monostable multivibrator

11. Waveforms

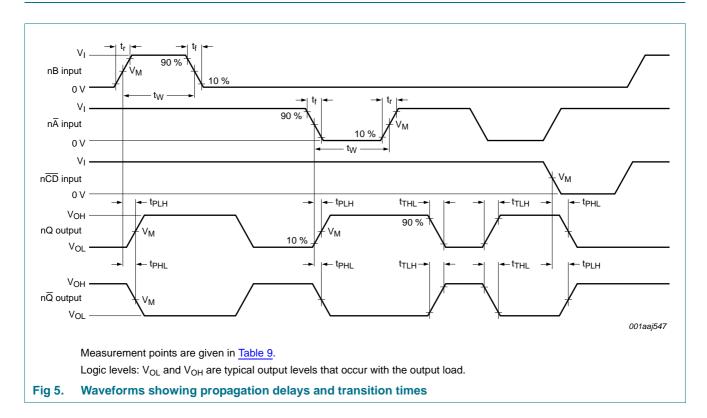


Table 9. Measurement points

Supply voltage	Input	Output
V_{DD}	V _M	V _M
5 V to 15 V	$0.5V_{DD}$	$0.5V_{DD}$

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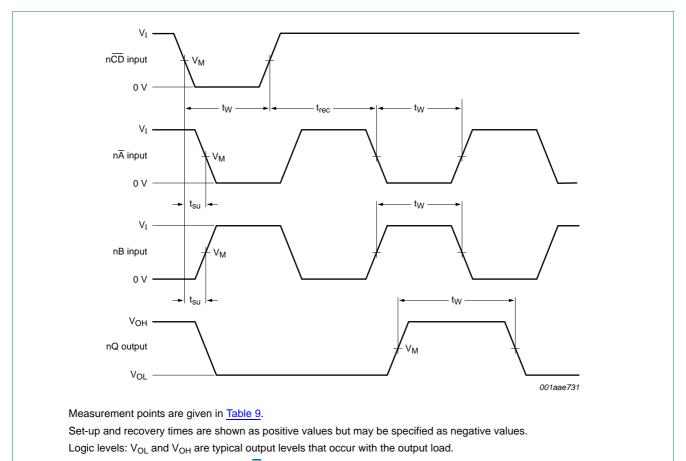
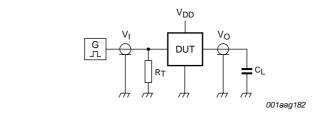


Fig 6. Waveforms showing minimum nA, nB, and nQ pulse widths and set-up and recovery times



Test data is given in Table 10.

Definitions for test circuit:

DUT = Device Under Test.

 C_L = load capacitance including jig and probe capacitance.

 R_T = termination resistance should be equal to the output impedance Z_0 of the pulse generator.

Fig 7. Test circuit for measuring switching times

Table 10. Test data

Supply voltage	Input		Load
V _{DD}	V _I	t _r , t _f	C _L
5 V to 15 V	V _{SS} or V _{DD}	≤ 20 ns	50 pF

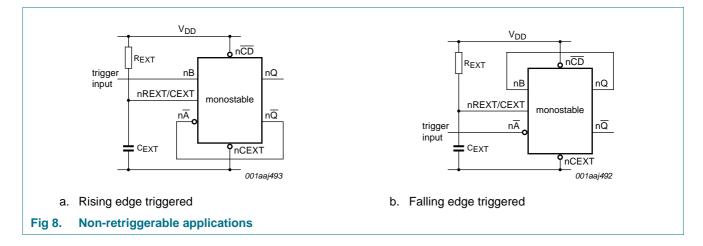
HEF4528B

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12. Application information

An example of a HEF4528B application is:

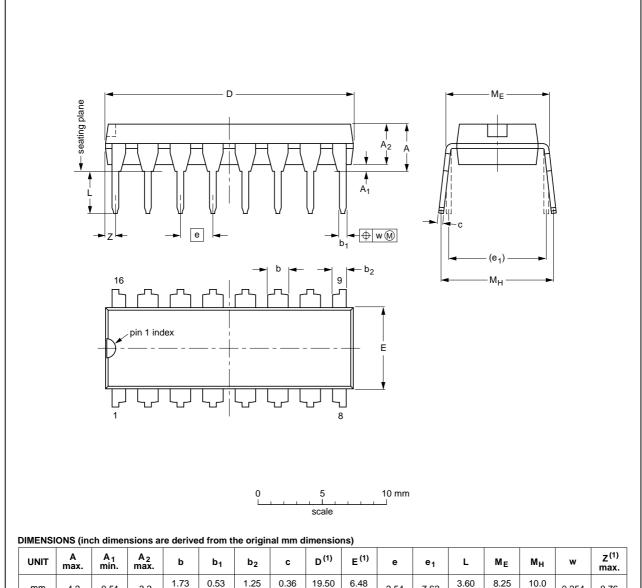
• Non-retriggerable monostable multivibrator



13. Package outline

DIP16: plastic dual in-line package; 16 leads (300 mil)

SOT38-4



UNIT	A max.	A ₁ min.	A ₂ max.	b	b ₁	b ₂	С	D ⁽¹⁾	E ⁽¹⁾	е	e ₁	L	ME	Мн	w	Z ⁽¹⁾ max.
mm	4.2	0.51	3.2	1.73 1.30	0.53 0.38	1.25 0.85	0.36 0.23	19.50 18.55	6.48 6.20	2.54	7.62	3.60 3.05	8.25 7.80	10.0 8.3	0.254	0.76
inches	0.17	0.02	0.13	0.068 0.051	0.021 0.015	0.049 0.033	0.014 0.009	0.77 0.73	0.26 0.24	0.1	0.3	0.14 0.12	0.32 0.31	0.39 0.33	0.01	0.03

Note

1. Plastic or metal protrusions of 0.25 mm (0.01 inch) maximum per side are not included.

OUTLINE		REFER	EUROPEAN	ISSUE DATE			
VERSION	IEC	JEDEC	JEITA		PROJECTION	ISSUE DATE	
SOT38-4						95-01-14 03-02-13	

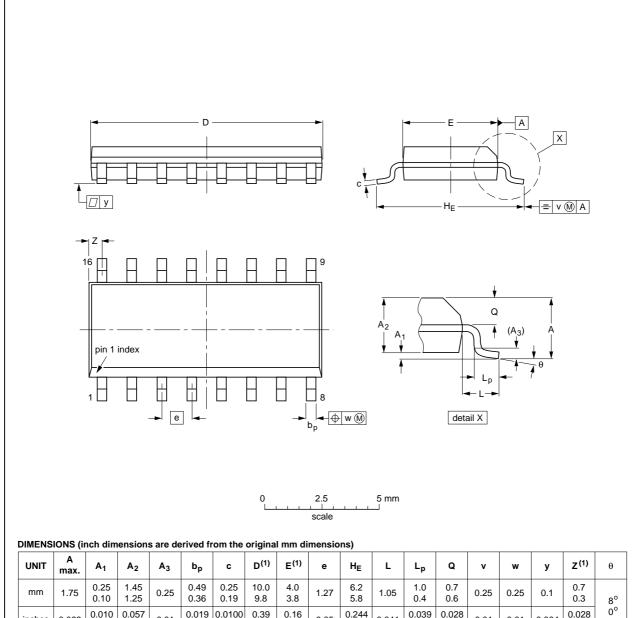
Fig 9. Package outline SOT38-4 (DIP16)

HEF4528B

HEF4528B NXP Semiconductors

SO16: plastic small outline package; 16 leads; body width 3.9 mm

SOT109-1



UNIT	A max.	A ₁	A ₂	A ₃	bp	С	D ⁽¹⁾	E ⁽¹⁾	е	HE	L	Lp	Q	v	w	у	Z ⁽¹⁾	θ
mm	1.75	0.25 0.10	1.45 1.25	0.25	0.49 0.36	0.25 0.19	10.0 9.8	4.0 3.8	1.27	6.2 5.8	1.05	1.0 0.4	0.7 0.6	0.25	0.25	0.1	0.7 0.3	8°
inches	0.069	0.010 0.004	0.057 0.049	0.01	1	0.0100 0.0075	0.39 0.38	0.16 0.15	0.05	0.244 0.228	0.041	0.039 0.016		0.01	0.01	0.004	0.028 0.012	0°

Note

1. Plastic or metal protrusions of 0.15 mm (0.006 inch) maximum per side are not included.

OUTLINE		REFER	EUROPEAN	ISSUE DATE			
VERSION	IEC	JEDEC	JEITA		PROJECTION	ISSUE DATE	
SOT109-1	076E07	MS-012				99-12-27 03-02-19	

Fig 10. Package outline SOT109-1 (SO16)

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14. Revision history

Table 11. Revision history

	-			
Document ID	Release date	Data sheet status	Change notice	Supersedes
HEF4528B v.7	20111122	Product data sheet	-	HEF4528B v.6
Modifications:	 Section App 	olications removed		
	• Table 6: I _{OF}	_I minimum values changed t	o maximum	
HEF4528B v.6	20091127	Product data sheet	-	HEF4528B v.5
HEF4528B v.5	20090813	Product data sheet	-	HEF4528B v.4
HEF4528B v.4	20090209	Product data sheet	-	HEF4528B_CNV v.3
HEF4528B_CNV v.3	19950101	Product specification	-	HEF4528B_CNV v.2
HEF4528B_CNV v.2	19950101	Product specification	-	-

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15. Legal information

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Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design
- [2] The term 'short data sheet' is explained in section "Definitions"
- [3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL http://www.nxp.com.

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